

## CLAIMS:

1 I claim:

1. A process for manufacturing a plurality of MEMS devices on a first layer of material of a selected thickness comprising:

attaching said first layer of material to a backing layer of material;

defining features on each individual ones of said plurality of MEMS

devices with first lines having at least a first selected width;

defining boundary lines between individual ones of said plurality of MEMS devices with second lines having a width that is less than said first selected width;

simultaneously etching said first lines and said second lines until said first lines defining device features are etched through said selected thickness;

stopping said etching before said second lines defining boundaries are etched through said first selected thickness; and

separating said first layer with said plurality of devices attached together from said backing layer.

2. The process of Claim 1 and comprising further processing of said separated first layer.

3. The process of Claim 2 when said further processing comprising testing said devices while still attached together on said first layer.

4. The process of Claim 2 wherein said further processing comprises separating each individual device of said first layer from each other.
5. The process of Claim 1 wherein said further processing comprises cleaning said devices while still attached together subsequent to said separation step.
6. The process of Claim 1 and further comprising packing said separated wafer with said devices still attached together for storage or shipping.
7. The process of Claim 1 wherein said first width of said first lines have a ratio greater than 4:1 with respect to said width of said second lines.
8. The process of Claim 1 wherein said first selected width is at least about 50 $\mu$ m and said second width is about 10 $\mu$ m.
9. The process of Claim 1 wherein said first layer of material is selected from the group consisting of silicon, gallium arsenide, quartz and silicon carbide.
10. The process of Claim 9 wherein said first layer of material is silicon.

11. A process for manufacturing a plurality of gimbal mirror devices on a first layer of material of a selected thickness comprising:

attaching said first layer of material to a backing layer of material;

defining features on each individual ones of said plurality of gimbal mirror devices with first lines having at least a first selected width;

defining boundary lines between individual ones of said plurality of gimbal mirror devices with second lines having a width that is less than said first selected width;

simultaneously etching said first lines and said second lines until said first lines defining gimbal mirror features are etched through said first selected thickness;

stopping said etching before said second lines defining boundaries are etched through said first selected thickness; and

separating said first layer with said plurality of gimbal mirror devices attached together from said backing layer.

12. The process of Claim 11 further comprising testing individual devices defined on said first layer.

13. The process of Claim 11 further comprising separating each individual gimbal mirror device from said first layer.

14. The process of Claim 11 wherein said further processing comprises cleaning said gimbal mirror while still attached together subsequent to said step of separating said first layer from said backing layer.
15. The process of Claim 11 and further comprising packing said separated wafer with said devices still attached together for storage or shipping.
16. The process of Claim 11 wherein said first lines have a width at least equal to about 50 $\mu$ m and said second lines have a width of about 10 $\mu$ m.
17. The process of Claim 11 wherein said first layer is a silicon wafer.
18. A wafer defining a plurality of MEMS devices attached together comprising:  
at least two features of said MEMS devices separated by first lines etched completely through said wafer, said first line having at least a first selected width;  
second lines etched part way through said wafer defining individual ones of said plurality of MEMS devices, said second lines having a second width which is less than said first selected width.
19. The wafer of Claim 18 wherein said width of said first lines have a ratio greater than 4:1 with respect to said width of said second lines.
20. The wafer of Claim 18 wherein said first selected width is at least about 50 $\mu$ m and said second width is about 10 $\mu$ m.

21. A wafer defining a plurality of gimbal mirror devices attached together comprising:

at least two features of said gimbal mirror devices separated by first lines etched completely through said wafer, said first lines having at least a first selected width;

second lines etched part way through said wafer defining individual ones of said plurality of gimbal mirror devices, said second lines having a second width which is less than said first selected width.